Preferred Device

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

- Sensitive Gate Allows Triggering by Microcontrollers and other Logic Circuits
- Blocking Voltage to 800 Volts
- On-State Current Rating of 8 Amperes RMS at 80°C
- High Surge Current Capability 80 Amperes
- Rugged, Economical TO220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dv/dt 5 V/μsec Minimum at 110°C
- Device Marking: Logo, Device Type, e.g., MCRSD, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---------------------|-------------------|--------------------|
| Peak Repetitive Off–State Voltage(1) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open) | VDRM, VRRM | | Volts |
| MCR8SD MCR8SM MCR8SN | | 400 600 800 | |
| On-State RMS Current (180° Conduction Angles; T _C = 80°C) | I _{T(RMS)} | 8.0 | Amps |
| Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _J = 110°C) | ITSM | 80 | Amps |
| Circuit Fusing Consideration (t = 8.33 ms) | I ² t | 26.5 | A ² sec |
| Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C) | PGM | 5.0 | Watts |
| Forward Average Gate Power (t = 8.3 ms, T _C = 80°C) | PG(AV) | 0.5 | Watt |
| Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 80°C) | I _{GM} | 2.0 | Amps |
| Operating Junction Temperature Range | TJ | -40 to 110 | °C |
| Storage Temperature Range | T _{stg} | -40 to 150 | °C |

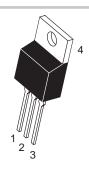
⁽¹⁾ VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



http://onsemi.com

SCRs 8 AMPERES RMS 400 thru 800 VOLTS





TO-220AB CASE 221A STYLE 3

| PIN ASSIGNMENT | | | |
|----------------|---------|--|--|
| 1 | Cathode | | |
| 2 | Anode | | |
| 3 | Gate | | |
| 4 | Anode | | |

ORDERING INFORMATION

| Device | Package | Shipping |
|--------|---------|---------------|
| MCR8SD | TO220AB | 50 Units/Rail |
| MCR8SM | TO220AB | 50 Units/Rail |
| MCR8SN | TO220AB | 50 Units/Rail |

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|--|-------------|------|
| Thermal Resistance — Junction to Case — Junction to Ambient | R _θ JC R _θ JA | 2.2 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | TL | 260 | °C |

ELECTRICAL CHARACTERISTICS (T_.I = 25°C unless otherwise noted)

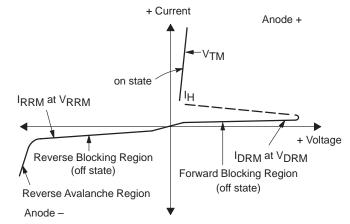
| Characteristic | Symbol | Min | Тур | Max | Unit | |
|---|---|--|----------|-----------|------------|-------|
| OFF CHARACTERISTICS | | | | | | |
| Peak Repetitive Forward or Reverse Blocking Current ⁽¹⁾ (V_D = Rated V_{DRM} and V_{RRM} ; R_{GK} = 1 $k\Omega$) | T _J = 25°C T _J = 110°C | I _{DRM} , I _{RRM} | _ | _ | 10 500 | μΑ |
| ON CHARACTERISTICS | | | | | | |
| Peak Forward On–State Voltage* (I _{TM} = 16 A) | | V _{TM} | T - | <u> </u> | 1.8 | Volts |
| Gate Trigger Current (Continuous dc) ⁽²⁾ $(V_D = 12 \text{ V}; R_L = 100 \Omega)$ | | lGT | 5.0 | 25 | 200 | μА |
| Holding Current ⁽²⁾ (V _D = 12 V, Gate Open, Initiating Current = 200 mA) | | lн | _ | 0.5 | 6.0 | mA |
| Latch Current(2) $(V_D = 12 \text{ V, I}_G = 200 \mu\text{A})$ | | ΙL | _ | 0.6 | 8.0 | mA |
| Gate Trigger Voltage (Continuous dc) ⁽²⁾ ($V_D = 12 \text{ V}; \text{ RL} = 100 \Omega$) | $T_{J} = 25^{\circ}C$ $T_{J} = -40^{\circ}C$ | VGT | 0.3 — | 0.65 — | 1.0 1.5 | Volts |
| Gate Non–Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega)$ | T _J = 110°C | V _{GD} | 0.2 | _ | _ | Volts |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Critical Rate of Rise of Off–State Voltage (V_D = 67% V_{DRM} , R_{GK} = 1 K Ω , C_{GK} = 0.1 μ F, T_J = 110°C) | | dv/dt | 5.0 | 15 | _ | V/µs |
| Critical Rate of Rise of On–State Current IPK = 50 A, Pw = 40 µsec, diG/dt = 1 A/µsec, Igt = 10 mA | | di/dt | | _ | 100 | A/μs |

^{*}Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

⁽¹⁾ R_{GK} = 1000 Ohms included in measurement. (2) Does not include R_{GK} in measurement.

Voltage Current Characteristic of SCR

| Symbol | Parameter |
|------------------|---|
| VDRM | Peak Repetitive Off State Forward Voltage |
| IDRM | Peak Forward Blocking Current |
| VRRM | Peak Repetitive Off State Reverse Voltage |
| I _{RRM} | Peak Reverse Blocking Current |
| V _{TM} | Peak On State Voltage |
| lΗ | Holding Current |



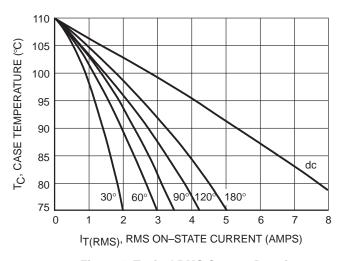


Figure 1. Typical RMS Current Derating

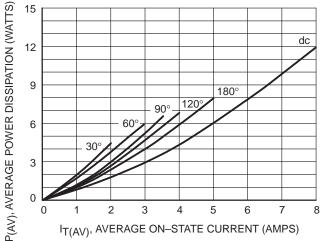


Figure 2. On-State Power Dissipation

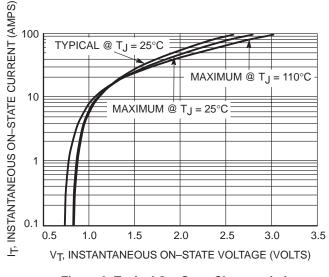


Figure 3. Typical On-State Characteristics

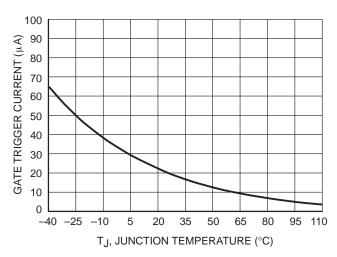
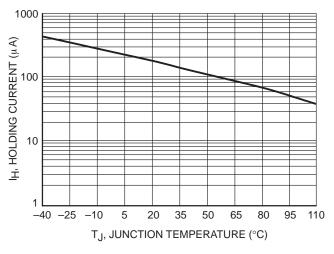


Figure 4. Typical Gate Trigger Current versus
Junction Temperature



1.0 V_{GT}, GATE TRIGGER VOLTAGE (VOLTS) 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 -40 -25 -10 5 20 35 50 65 95 110 T_J, JUNCTION TEMPERATURE (°C)

Figure 5. Typical Holding Current versus Junction Temperature

Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

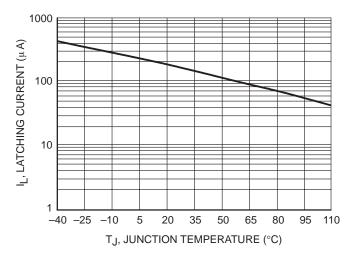
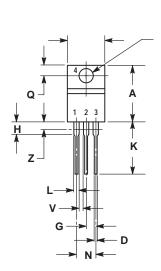
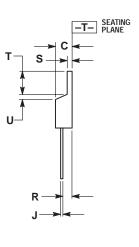


Figure 7. Typical Latching Current versus Junction Temperature

PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 **ISSUE Z**



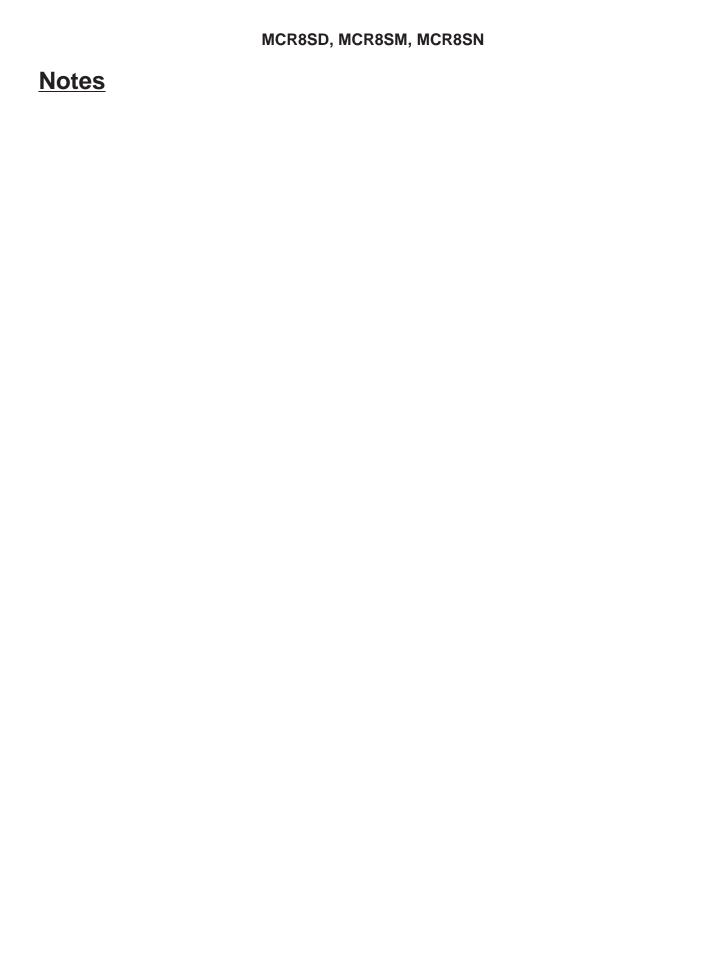


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INC | HES | MILLIMETER | |
|-----|-------|-------|------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.405 | 9.66 | 10.28 |
| С | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

- STYLE 3:
 PIN 1. CATHODE
 2. ANODE
 3. GATE
 4. ANODE





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